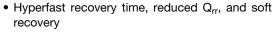


Hyperfast Rectifier, 2 x 5 A FRED Pt®



PRODUCT SUMMARY				
Package	TO-263AC (SMPD)			
I _{F(AV)}	2 x 5 A			
V_{R}	600 V			
V _F at I _F	1 V			
t _{rr}	35 ns			
T _J max.	175 °C			
Diode variation	Dual die			

FEATURES





RoHS

COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- For PFC CRM / CCM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		600	V
A	per device	I _{F(AV)}	T _{solder pad} = 153 °C	10	
Average rectified forward current	per diode			5	۸
per device		T 05 °C 6 ma aguara nulas	110	А	
Non-repetitive peak surge current	per diode	IFSM	$T_J = 25$ °C, 6 ms square pulse	60	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-	
Forward voltage, per diode V _F	M	I _F = 5 A	-	1.2	1.5	V
	I _F = 5 A, T _J = 150 °C	-	1	1.25		
Developed to the second	I _R	$V_R = V_R$ rated	-	-	3	
Reverse leakage current, per diode		T _J = 150 °C, V _R = V _R rated	-	15	150	μΑ
Junction capacitance, per diode	C _T	V _R = 600 V	-	6	-	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50 A$	Vμs, V _R = 30 V	-	35	-	
Payaraa raaayany tima	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	35	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 5 A, dI _F /dt = 500 A/μs, V _R = 400 V	-	45	-	ns
		T _J = 125 °C		-	70	-	
Peak recovery current		T _J = 25 °C		-	7	-	^
	I _{RRM}	T _J = 125 °C		-	10	-	Α
Devices and a second of the second	0	T _J = 25 °C		-	160	-	nC
Reverse recovery charge	Q_{rr}	T _J = 125 °C		-	370	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C
Thermal resistance, per diode junction to solder pad	R _{thJ-Sp}		-	2.4	3.3	°C/W
Approximate weight				0.55		g
Approximate weight				0.02		oz.
Marking device		Case style TO-263AC (SMPD)		10CI	DH06	

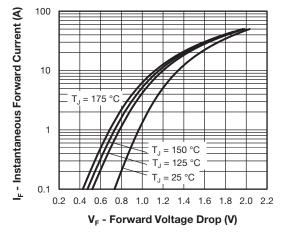


Fig. 1 - Typical Forward Voltage Drop Characteristics

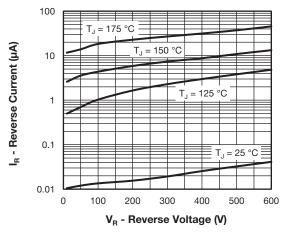


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

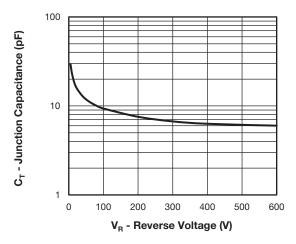


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

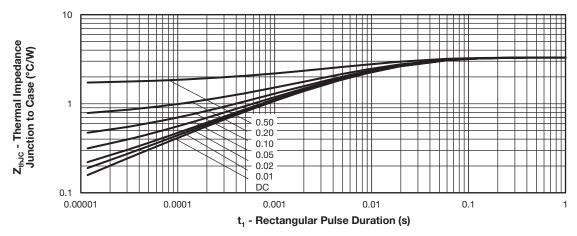


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

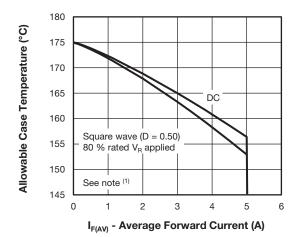


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

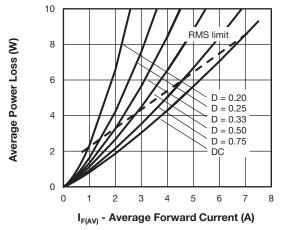


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = rated V_R$

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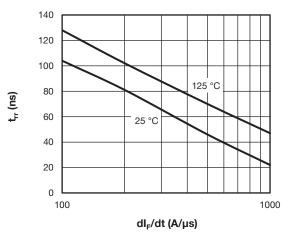


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

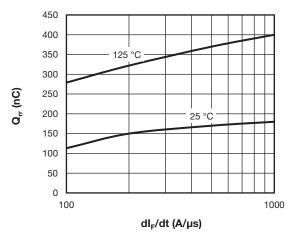
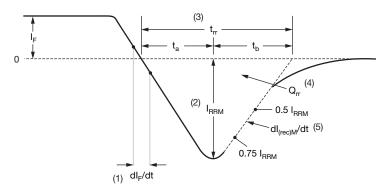


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

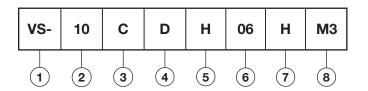
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (10 A)

3 - Circuit configuration:

C = common cathode

4 - D = SMPD package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (06 = 600 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

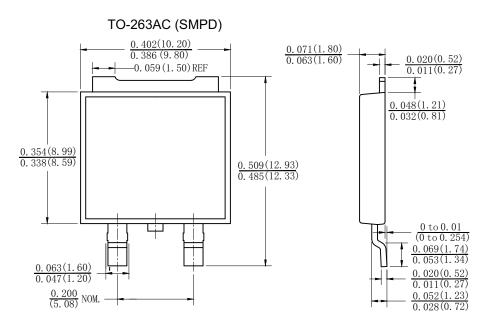
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-10CDH06HM3/I	2000	2000	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95604				
Part marking information <u>www.vishay.com/doc?95566</u>				
Packaging information	www.vishay.com/doc?88869			

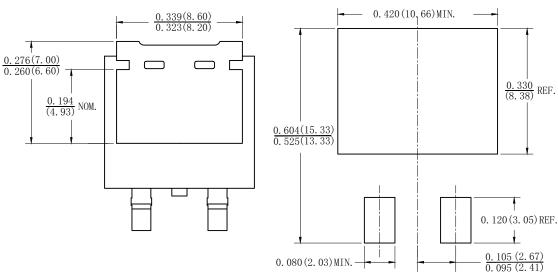


TO-263AC (SMPD)

DIMENSIONS in inches (millimeters)



Mounting Pad Layout





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Vishay

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